

Six-Pack Trench IGBT

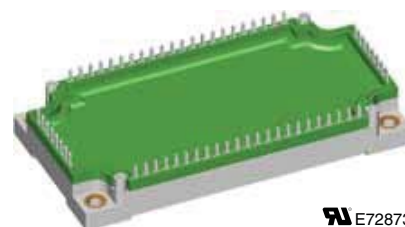
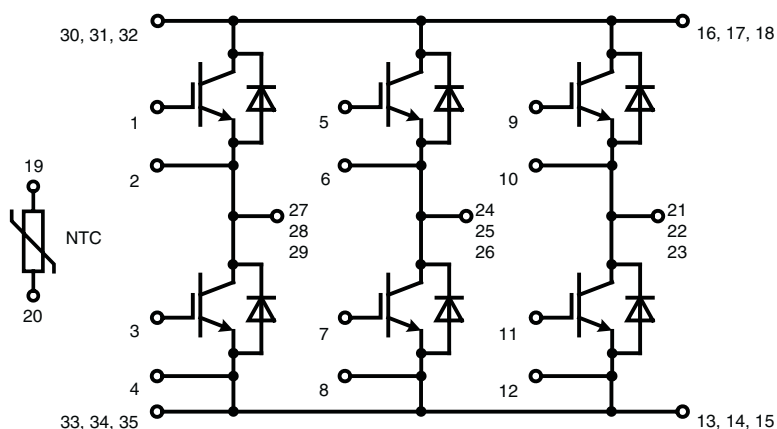
$$V_{CES} = 1200 \text{ V}$$

$$I_{C25} = 145 \text{ A}$$

$$V_{CE(sat)} = 1.7 \text{ V}$$

Part name (Marking on product)

MWI100-12T8T



E72873

Pin configuration see outlines.

Features:

- Trench IGBT technology
- low saturation voltage
- low switching losses
- square RBSOA, no latch up
- high short circuit capability
- positive temperature coefficient for easy paralleling
- MOS input, voltage controlled
- ultra fast free wheeling diodes
- solderable pins for PCB mounting
- package with copper base plate

Application:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies

Package:

- "E3-Pack" standard outline
- Insulated copper base plate
- Soldering pins for PCB mounting
- Temperature sense included

Output Inverter T1 - T6

				Ratings			
Symbol	Definitions	Conditions	min.	typ.	max.	Unit	
V _{CES}	collector emitter voltage	T _{VJ} = 25°C			1200	V	
V _{GES}	max. DC gate voltage	continuous			±20	V	
V _{GEM}	max. transient collector gate voltage	transient			±30	V	
I _{C25}	collector current	T _C = 25°C			145	A	
I _{C80}		T _C = 80°C			100	A	
P _{tot}	total power dissipation	T _C = 25°C			480	W	
V _{CE(sat)}	collector emitter saturation voltage	I _C = 100 A; V _{GE} = 15 V	T _{VJ} = 25°C T _{VJ} = 125°C	1.7 2.0	2.1	V V	
V _{GE(th)}	gate emitter threshold voltage	I _C = 4 mA; V _{GE} = V _{CE}	T _{VJ} = 25°C	5.0	5.8	6.5	V
I _{CES}	collector emitter leakage current	V _{CE} = V _{CES} ; V _{GE} = 0 V	T _{VJ} = 25°C T _{VJ} = 125°C		4	mA mA	
I _{GES}	gate emitter leakage current	V _{GE} = ±20 V			500	nA	
C _{ies}	input capacitance	V _{CE} = 25 V; V _{GE} = 0 V; f = 1 MHz		7210		pF	
Q _{G(on)}	total gate charge	V _{CE} = 600 V; V _{GE} = 15 V; I _C = 100 A		550		nC	
t _{d(on)}	turn-on delay time	inductive load V _{CE} = 600 V; I _C = 100 A V _{GE} = ±15 V; R _G = 3.9 Ω	T _{VJ} = 125°C	270		ns	
t _r	current rise time			50		ns	
t _{d(off)}	turn-off delay time			400		ns	
t _f	current fall time			340		ns	
E _{on}	turn-on energy per pulse			8.5		mJ	
E _{off}	turn-off energy per pulse			13.5		mJ	
RBSOA	reverse bias safe operating area	V _{GE} = ±15 V; R _G = 3.9 Ω;	T _{VJ} = 125°C V _{CEK} = 1200 V		200	A	
SCSOA	short circuit safe operating area						
t _{sc}	short circuit duration	V _{CE} = 900 V; V _{GE} = ±15 V;	T _{VJ} = 125°C		10	μs	
I _{sc}	short circuit current	R _G = 3.9 Ω; non-repetitive		400		A	
R _{thJC}	thermal resistance junction to case	(per IGBT)			0.26	K/W	

Output Inverter D1 - D6

				Ratings		
Symbol	Definitions	Conditions	min.	typ.	max.	Unit
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200	V
I_{F25}	forward current	$T_C = 25^{\circ}\text{C}$			135	A
I_{F80}		$T_C = 80^{\circ}\text{C}$			90	A
V_F	forward voltage	$I_F = 100\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.95 1.95	2.2	V V
Q_{rr}	reverse recovery charge	$V_R = 600\text{ V}$ $di_F/dt = -1600\text{ A}/\mu\text{s}$ $I_F = 100\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$	12.5		μC
I_{RM}	max. reverse recovery current			100		A
t_{rr}	reverse recovery time			350		ns
E_{rec}	reverse recovery energy			4		mJ
R_{thJC}	thermal resistance junction to case	(per diode)			0.4	K/W

 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

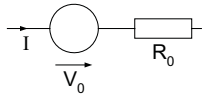
Temperature Sensor NTC

Symbol	Definitions	Conditions	Ratings			
			min.	typ.	max.	Unit
R_{25}	resistance	$T_C = 25^\circ\text{C}$	4.75	5.0	5.25	k Ω
$B_{25/50}$				3375		K

Module

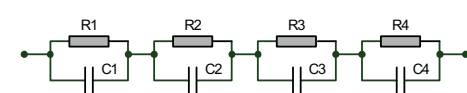
Symbol	Definitions	Conditions	Ratings			
			min.	typ.	max.	Unit
T_{VJ}	operating temperature		-40		125	$^\circ\text{C}$
T_{VJM}	max. virtual junction temperature				150	$^\circ\text{C}$
T_{stg}	storage temperature		-40		125	$^\circ\text{C}$
V_{ISOL}	isolation voltage	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$			2500	V~
CTI	comparative tracking index				200	
M_d	mounting torque (M5)		2.7		3.3	Nm
d_s	creep distance on surface		10			mm
d_A	strike distance through air		7.5			mm
$R_{pin-chip}$	resistance pin to chip			2.5		m Ω
R_{thCH}	thermal resistance case to heatsink	with heatsink compound		0.02		K/W
Weight				300		g

0.0 Equivalent Circuits for Simulation



Ratings

Symbol	Definitions	Conditions	min.	typ.	max.	Unit
V_0	IGBT	T1 - T6	$T_{VJ} = 125^\circ\text{C}$	1.0		V
R_0				9.1		m Ω
V_0	Diode	D1 - D6	$T_{VJ} = 150^\circ\text{C}$	1.09		V
R_0				9.1		m Ω



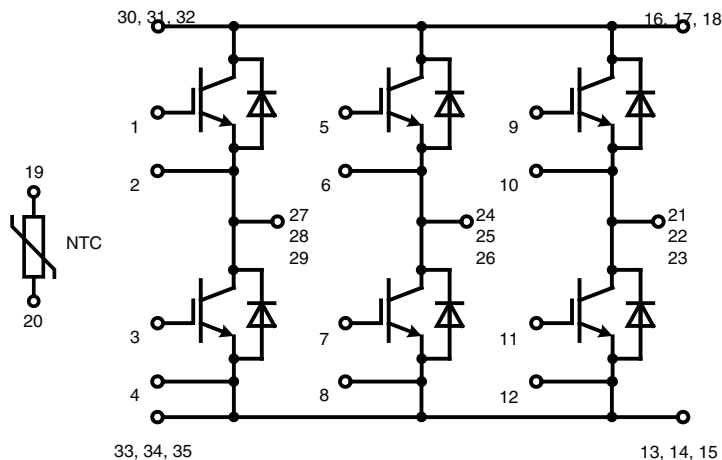
$$Z_{th}(t) = \sum_{i=1}^n \left[R_i \cdot \left(1 - \exp\left(-\frac{t}{\tau_i}\right) \right) \right]$$

$$\tau_i = R_i \cdot C_i$$

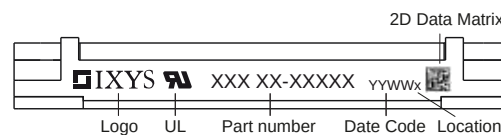
	IGBT	Diode
R_1	0.03985	0.084
R_2	0.05038	0.069
R_3	0.08959	0.146
R_4	0.08018	0.101
τ_1	0.0025	0.0025
τ_2	0.076	0.076
τ_3	0.036	0.036
τ_4	0.076	0.076

$T_C = 25^\circ\text{C}$ unless otherwise stated

Circuit Diagram

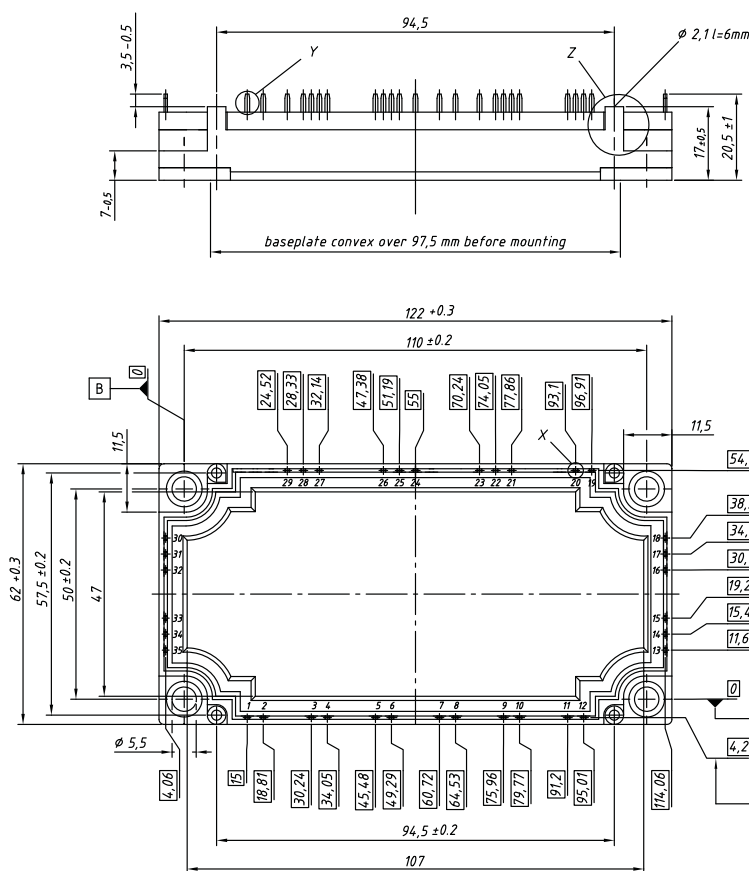


Marking on Product

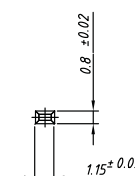


Outline Drawing

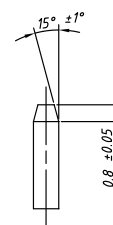
Dimensions in mm (1 mm = 0.0394")



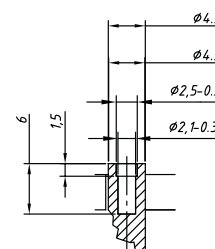
Detail X



Detail Y



Detail Z



Product Marking

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MWI100-12T8T	MWI100-12T8T	Box	5	502294

Inverter T1 - T6

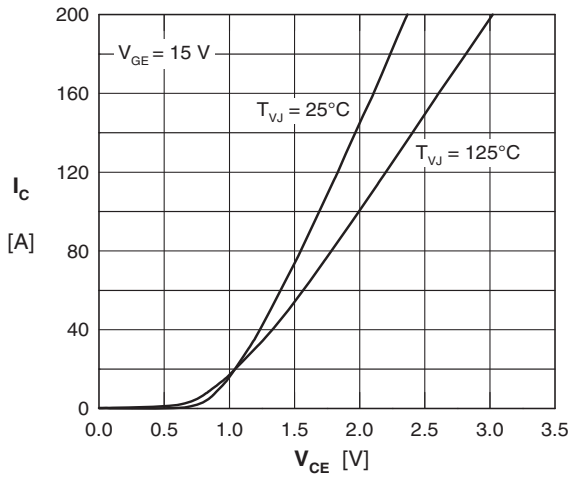


Fig. 1 Typ. output characteristics

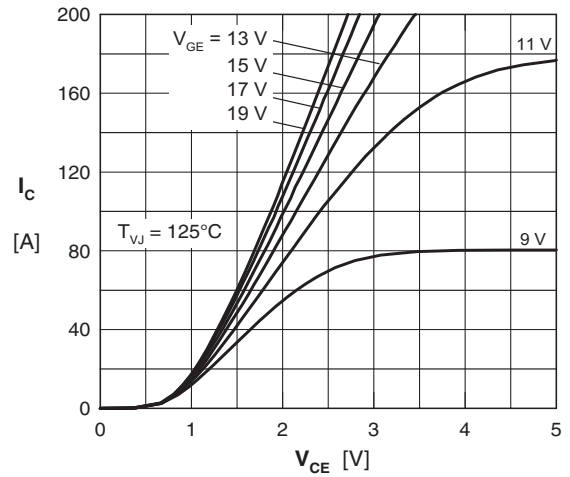


Fig. 2 output characteristics

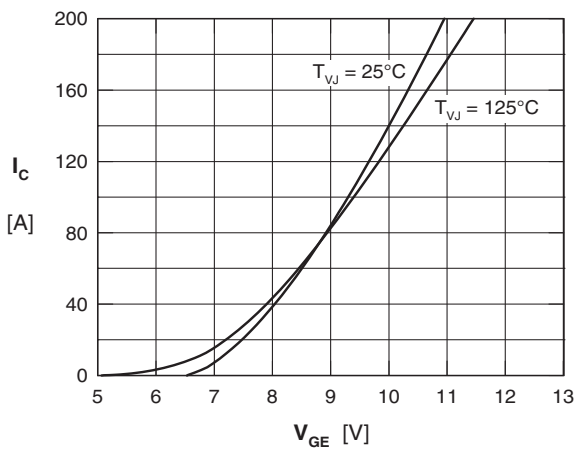


Fig. 3 Typ. transfer characteristics

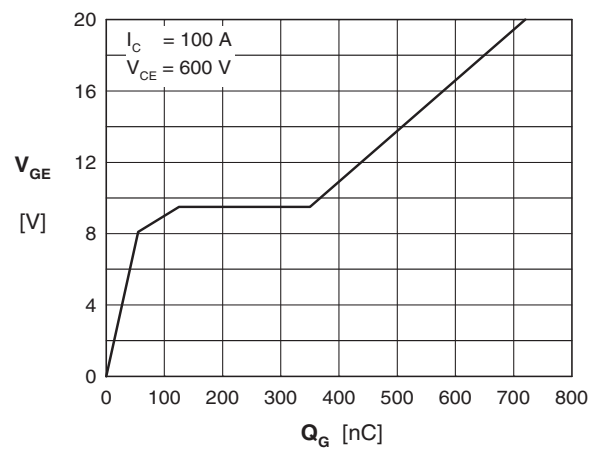


Fig. 4 Typ. turn-on gate charge

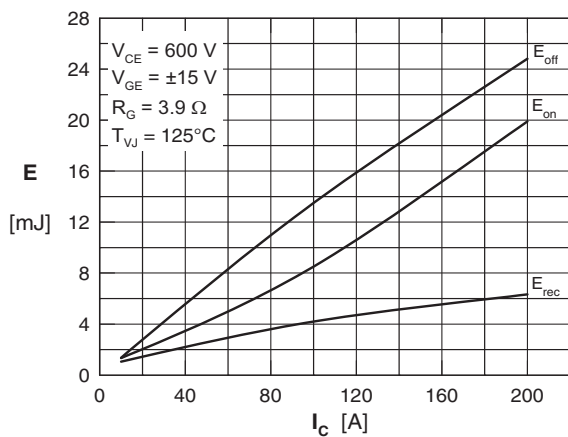


Fig. 5 Typ. switching energy vs. collector current

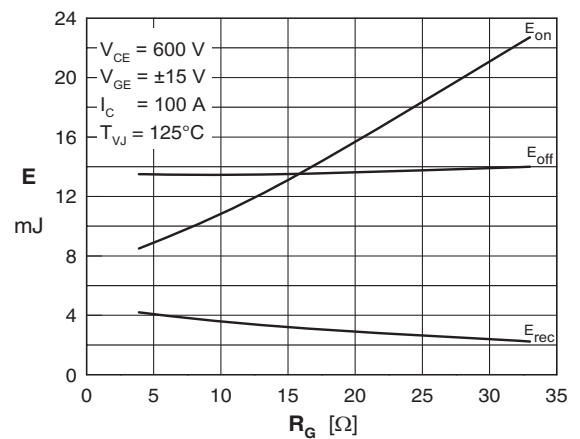


Fig. 6 Typ. switching energy vs. gate resistance

Inverter D1 - D6

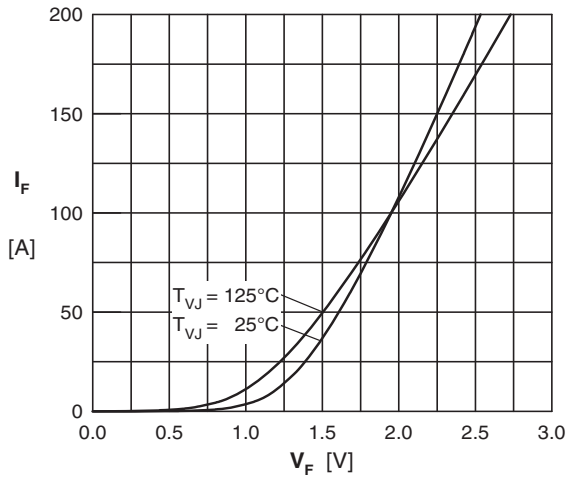


Fig. 7 Typ. Forward current versus V_F

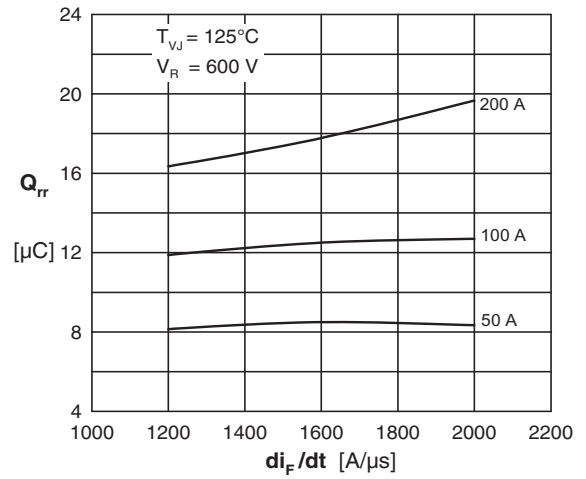


Fig. 8 Typ. reverse recov.charge Q_{rr} vs. di/dt

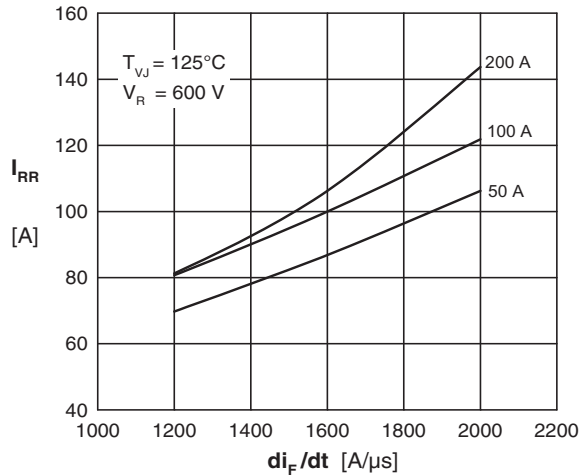


Fig. 9 Typ. peak reverse current I_{RM} vs. di/dt

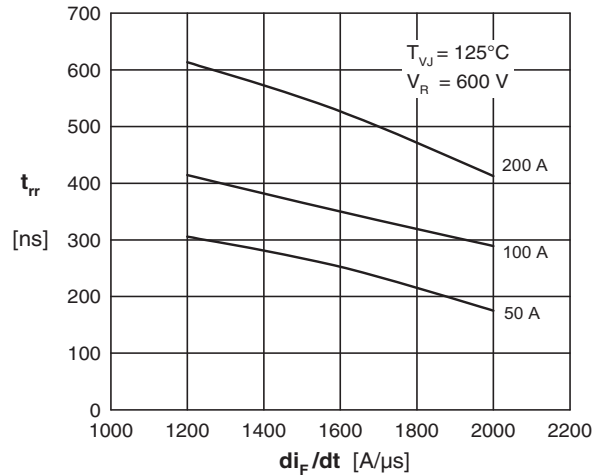


Fig. 10 Typ. recovery time t_{rr} versus di/dt

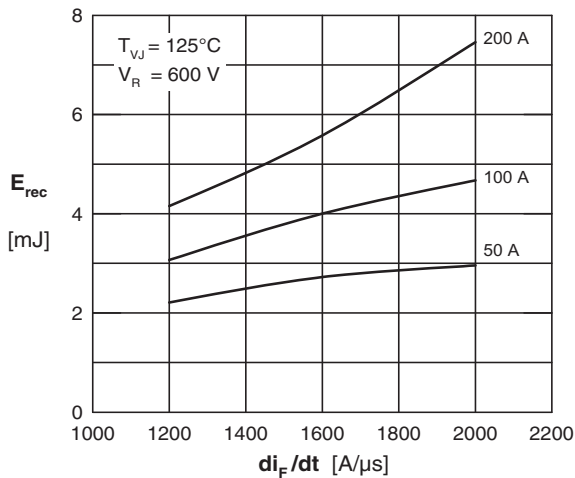


Fig. 11 Typ. recovery energy E_{rec} versus di/dt

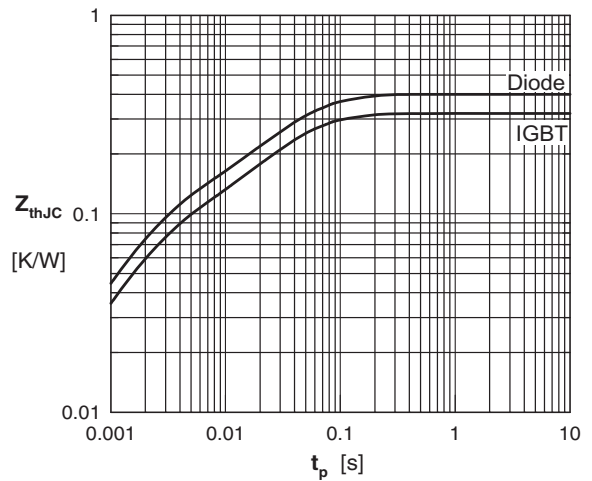


Fig. 12 Typ. transient thermal impedance

NTC

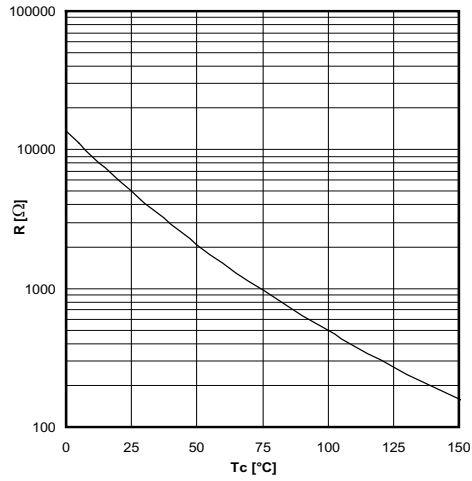


Fig. 13 Typ. NTC resistance vs. temperature